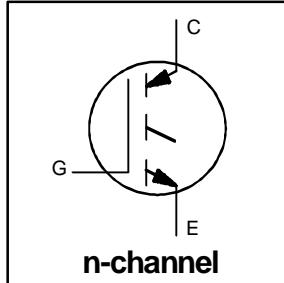


Features

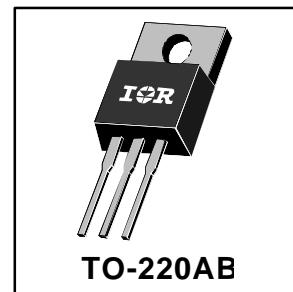
- Switching-loss rating includes all "tail" losses
- Optimized for line frequency operation (to 400 Hz)
See Fig. 1 for Current vs. Frequency curve



$V_{CES} = 600V$
 $V_{CE(sat)} \leq 1.8V$
 @ $V_{GE} = 15V$, $I_C = 31A$

Description

Insulated Gate Bipolar Transistors (IGBTs) from International Rectifier have higher usable current densities than comparable bipolar transistors, while at the same time having simpler gate-drive requirements of the familiar power MOSFET. They provide substantial benefits to a host of high-voltage, high-current applications.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	50	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	31	
I_{CM}	Pulsed Collector Current ①	240	
I_{LM}	Clamped Inductive Load Current ②	100	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	15	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	160	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	65	
T_J	Operating Junction and	-55 to $+150$	$^\circ C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	0.77	$^\circ C/W$
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	80	
Wt	Weight	—	2.0 (0.07)	—	g (oz)

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(\text{BR})\text{CES}}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{\text{GE}} = 0\text{V}, I_C = 250\mu\text{A}$
$V_{(\text{BR})\text{ECS}}$	Emitter-to-Collector Breakdown Voltage ^④	20	—	—	V	$V_{\text{GE}} = 0\text{V}, I_C = 1.0\text{A}$
$\Delta V_{(\text{BR})\text{CES}/\Delta T_J}$	Temp. Coeff. of Breakdown Voltage	—	0.75	—	V/ $^\circ\text{C}$	$V_{\text{GE}} = 0\text{V}, I_C = 1.0\text{mA}$
$V_{\text{CE}(\text{on})}$	Collector-to-Emitter Saturation Voltage	—	1.6	1.8	V	$I_C = 31\text{A}$ $V_{\text{GE}} = 15\text{V}$
		—	2.2	—		$I_C = 60\text{A}$ See Fig. 2, 5
		—	1.7	—		$I_C = 31\text{A}, T_J = 150^\circ\text{C}$
		3.0	—	5.5		$V_{\text{CE}} = V_{\text{GE}}, I_C = 250\mu\text{A}$
$\Delta V_{\text{GE}(\text{th})}/\Delta T_J$	Temp. Coeff. of Threshold Voltage	—	-9.3	—	mV/ $^\circ\text{C}$	$V_{\text{CE}} = V_{\text{GE}}, I_C = 250\mu\text{A}$
g_{fe}	Forward Transconductance ^⑤	12	21	—	S	$V_{\text{CE}} = 100\text{V}, I_C = 31\text{A}$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{\text{GE}} = 0\text{V}, V_{\text{CE}} = 600\text{V}$
		—	—	1000	μA	$V_{\text{GE}} = 0\text{V}, V_{\text{CE}} = 600\text{V}, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{\text{GE}} = \pm 20\text{V}$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	62	90	nC	$I_C = 31\text{A}$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	10	15		$V_{\text{CC}} = 400\text{V}$ See Fig. 8
Q_{gc}	Gate - Collector Charge (turn-on)	—	27	40		$V_{\text{GE}} = 15\text{V}$
$t_{d(\text{on})}$	Turn-On Delay Time	—	28	—	ns	$T_J = 25^\circ\text{C}$
t_r	Rise Time	—	50	—		$I_C = 31\text{A}, V_{\text{CC}} = 480\text{V}$
$t_{d(\text{off})}$	Turn-Off Delay Time	—	1100	1500		$V_{\text{GE}} = 15\text{V}, R_G = 10\Omega$
t_f	Fall Time	—	620	1100		Energy losses include "tail"
E_{on}	Turn-On Switching Loss	—	1.0	—	mJ	See Fig. 9, 10, 11, 14
E_{off}	Turn-Off Switching Loss	—	12	—		
E_{ts}	Total Switching Loss	—	13	20		
$t_{d(\text{on})}$	Turn-On Delay Time	—	29	—	ns	$T_J = 150^\circ\text{C},$ $I_C = 31\text{A}, V_{\text{CC}} = 480\text{V}$
t_r	Rise Time	—	53	—		$V_{\text{GE}} = 15\text{V}, R_G = 10\Omega$
$t_{d(\text{off})}$	Turn-Off Delay Time	—	1600	—		Energy losses include "tail"
t_f	Fall Time	—	1200	—		See Fig. 10, 14
E_{ts}	Total Switching Loss	—	22	—	mJ	Measured 5mm from package
L_E	Internal Emitter Inductance	—	7.5	—	nH	
C_{ies}	Input Capacitance	—	1600	—	pF	$V_{\text{GE}} = 0\text{V}$ $V_{\text{CC}} = 30\text{V}$ See Fig. 7 $f = 1.0\text{MHz}$
C_{oes}	Output Capacitance	—	140	—		
C_{res}	Reverse Transfer Capacitance	—	20	—		

Notes:

- ① Repetitive rating; $V_{\text{GE}}=20\text{V}$, pulse width limited by max. junction temperature.
(See fig. 13b)
- ② $V_{\text{CC}}=80\%(V_{\text{CES}})$, $V_{\text{GE}}=20\text{V}$, $L=10\mu\text{H}$, $R_G=10\Omega$, (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width $\leq 80\mu\text{s}$; duty factor $\leq 0.1\%$.
- ⑤ Pulse width $5.0\mu\text{s}$, single shot.

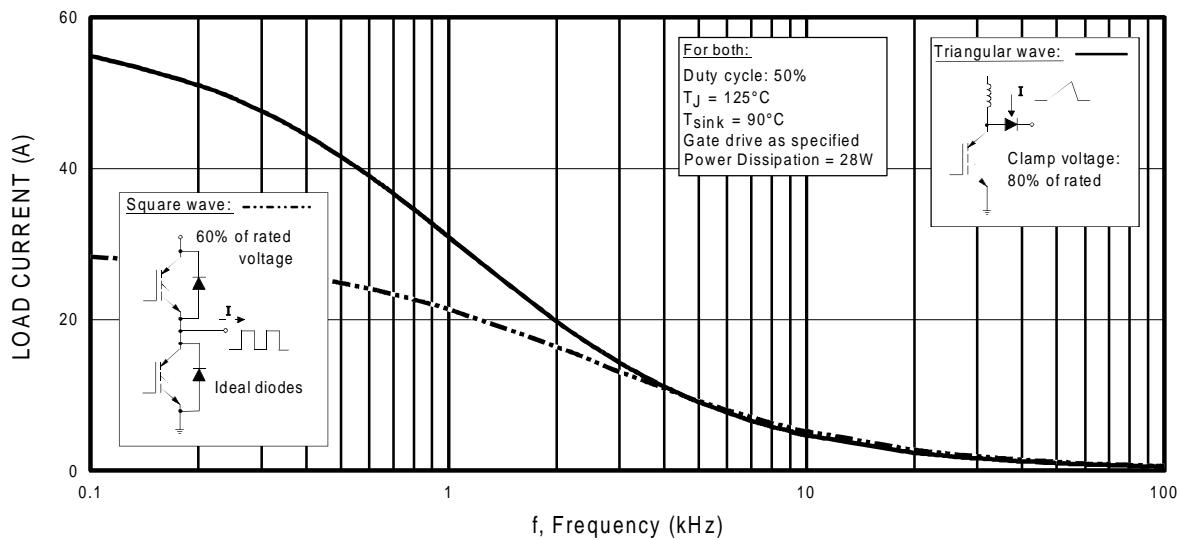


Fig. 1 - Typical Load Current vs. Frequency
 (For square wave, $I=I_{\text{RMS}}$ of fundamental; for triangular wave, $I=I_{\text{PK}}$)

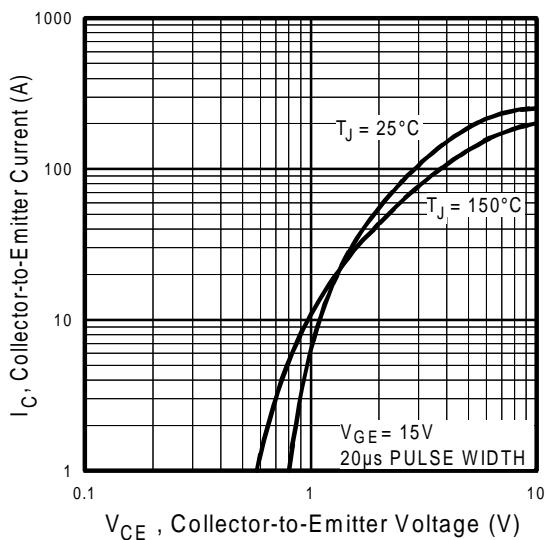


Fig. 2 - Typical Output Characteristics

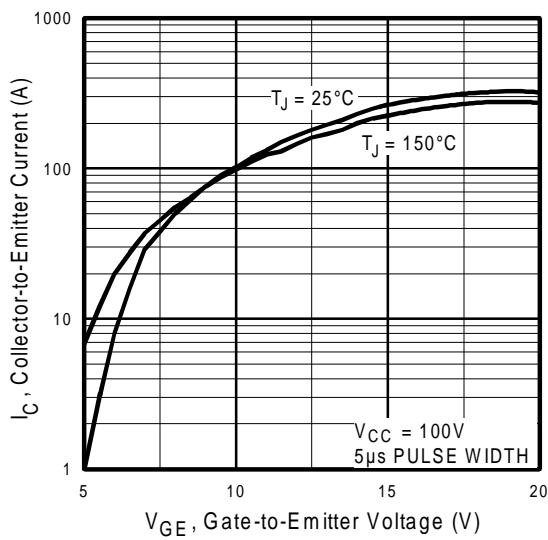


Fig. 3 - Typical Transfer Characteristics

IRGBC40S

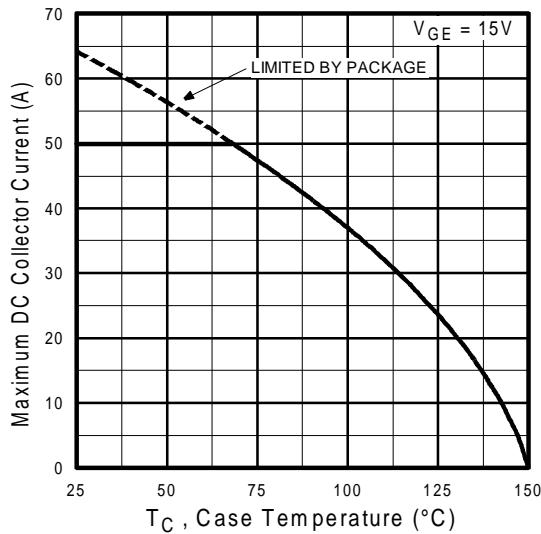


Fig. 4 - Maximum Collector Current vs. Case Temperature

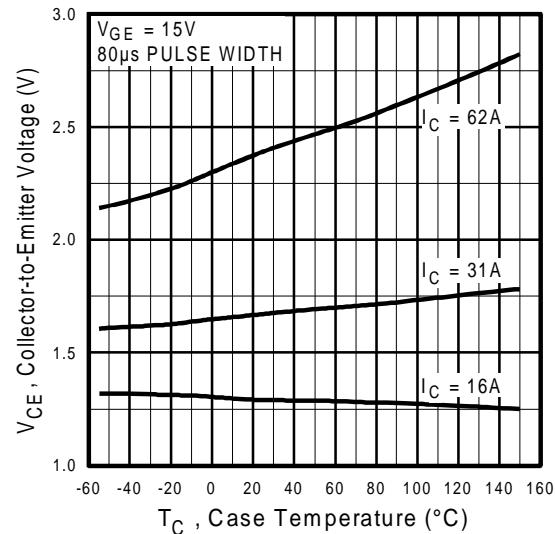


Fig. 5 - Collector-to-Emitter Voltage vs. Case Temperature

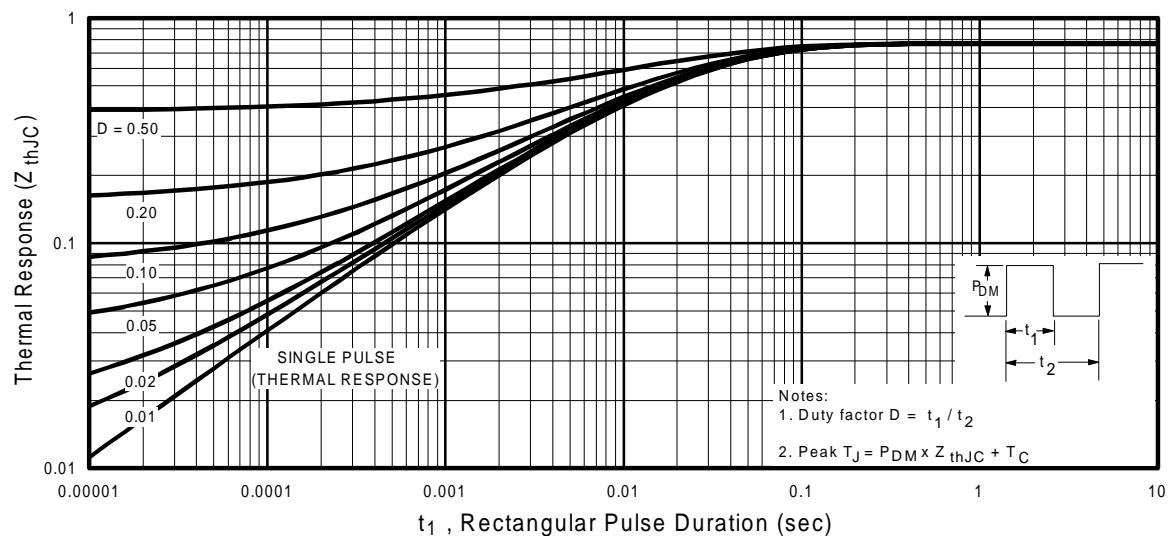


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

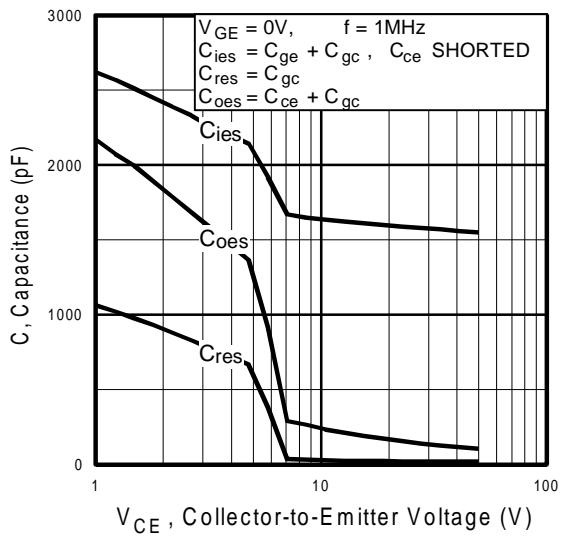


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

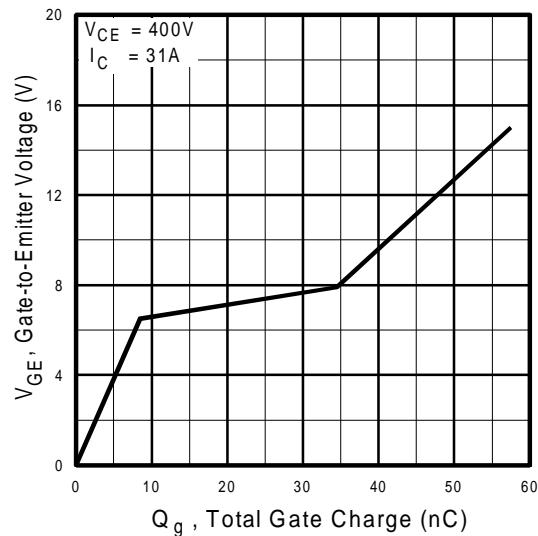


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

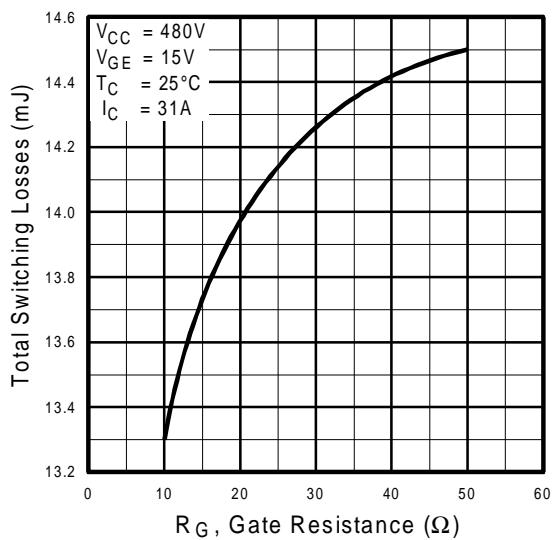


Fig. 9 - Typical Switching Losses vs. Gate Resistance

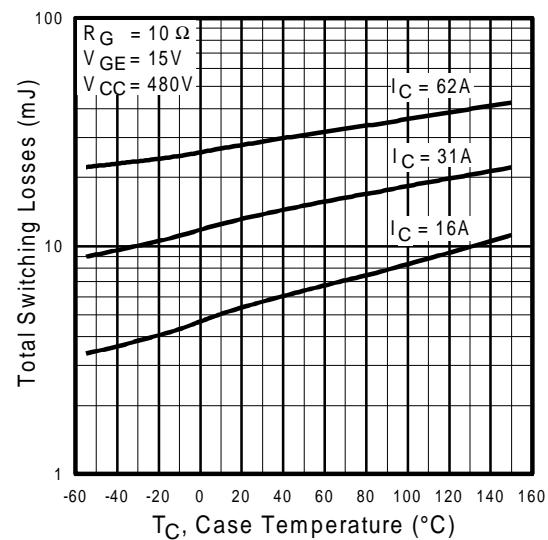


Fig. 10 - Typical Switching Losses vs. Case Temperature

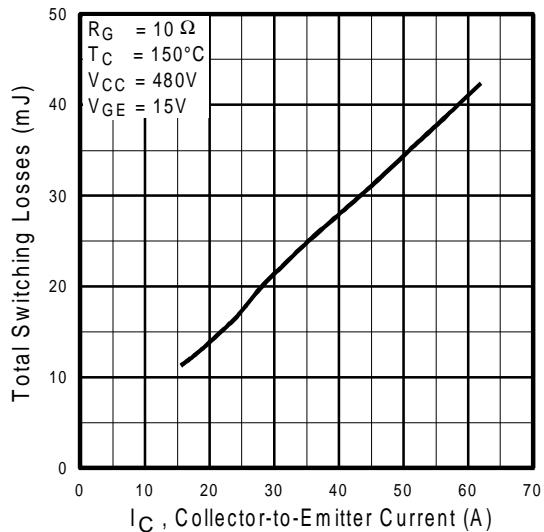


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

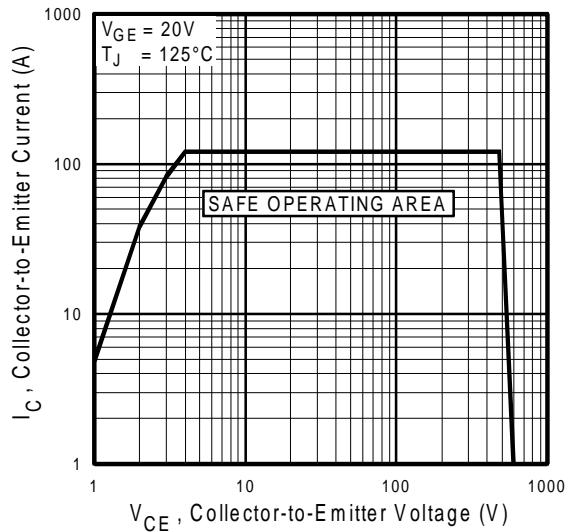


Fig. 12 - Turn-Off SOA

Refer to Section D for the following:

Appendix C: Section D - page D-5

- Fig. 13a - Clamped Inductive Load Test Circuit
- Fig. 13b - Pulsed Collector Current Test Circuit
- Fig. 14a - Switching Loss Test Circuit
- Fig. 14b - Switching Loss Waveform

Package Outline 1 - JEDEC Outline TO-220AB

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